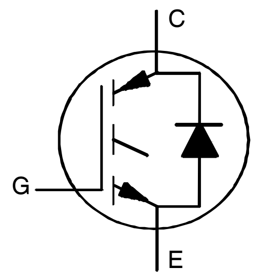
International
IOR Rectifier

AUTOMOTIVE GRADE

AUIRGP4066D1
AUIRGP4066D1-E

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE



n-channel

V_{CES} = 600V

$I_{C(Nominal)}$ = 75A

$t_{SC} \geq$ 5μs, $T_{J(max)}$ = 175°C

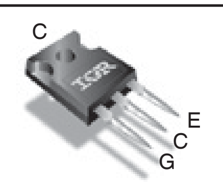
$V_{CE(on)}$ typ. = 1.70V

Features

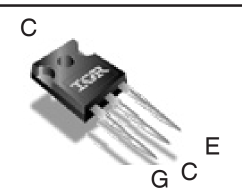
- Low $V_{CE\,(ON)}$ Trench IGBT Technology
- Low switching losses
- Maximum Junction temperature 175 °C
- 5 μS short circuit SOA
- Square RBSOA
- 100% of the parts tested for 4X rated current (I_{LM})①
- Positive $V_{CE\,(ON)}$ Temperature Coefficient
- Soft Recovery Co-Pak Diode
- Tight parameter distribution
- Lead-Free, RoHS Compliant
- Automotive Qualified *

Benefits

- High Efficiency in a wide range of applications
- Suitable for a wide range of switching frequencies due to Low $V_{CE\,(ON)}$ and Low Switching losses
- Rugged transient Performance for increased reliability
- Excellent Current sharing in parallel operation
- Low EMI



TO-247AC
AUIRGP4066D1



TO-247AD
AUIRGP4066D1-E

G	C	E
Gate	Collector	Emitter

Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied.Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	140⑤	A
I_C @ T_C = 100°C	Continuous Collector Current	90	
$I_{NOMINAL}$	Nominal Current	75	
I_{CM}	Pulse Collector Current V_{GE} = 15V	225	
I_{LM}	Clamped Inductive Load Current V_{GE} = 20V ①	300	
$I_{F\ NOMINAL}$	Diode Nominal Current②	75⑤	
I_{FM}	Diode Maximum Forward Current ②	300	
V_{GE}	Continuous Gate-to-Emitter Voltage	±20	V
	Transient Gate-to-Emitter Voltage	±30	
P_D @ T_C = 25°C	Maximum Power Dissipation	454	W
P_D @ T_C = 100°C	Maximum Power Dissipation	227	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case-(each IGBT) ④	—	—	0.33	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case-(each Diode)④	—	—	0.53	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	—	0.24	—	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	—	40	—	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V_{GE} = 0V, I_C = 200µA ④
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.30	—	V/°C	V_{GE} = 0V, I_C = 15mA (25°C-175°C)
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.70	2.1	V	I_C = 75A, V_{GE} = 15V, T_J = 25°C ②
		—	2.0	—		I_C = 75A, V_{GE} = 15V, T_J = 150°C②
		—	2.1	—		I_C = 75A, V_{GE} = 15V, T_J = 175°C②
$V_{GE(th)}$	Gate Threshold Voltage	4.0	—	6.5	V	V_{CE} = V_{GE}, I_C = 2.1mA
$\Delta V_{GE(th)}/\Delta TJ$	Threshold Voltage temp. coefficient	—	-13	—	mV/°C	V_{CE} = V_{GE}, I_C = 20mA (25°C - 175°C)
gfe	Forward Transconductance	—	50	—	S	V_{CE} = 50V, I_C = 75A, PW = 25µs
I_{CES}	Collector-to-Emitter Leakage Current	—	3.0	200	µA	V_{GE} = 0V, V_{CE} = 600V
		—	10	—	mA	V_{GE} = 0V, V_{CE} = 600V, T_J = 175°C
V_{FM}	Diode Forward Voltage Drop	—	1.60	1.77	V	I_F = 75A
		—	1.54	—		I_F = 75A, T_J = 175°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	150	225	nC	I_C = 75A
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	40	60		V_{GE} = 15V
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	60	90		V_{CC} = 400V
E_{on}	Turn-On Switching Loss	—	4240	5190	µJ	I_C = 75A, V_{CC} = 400V, V_{GE} = 15V
E_{off}	Turn-Off Switching Loss	—	2170	3060		R_G = 10Ω, L = 100µH, T_J = 25°C
E_{total}	Total Switching Loss	—	6410	8250		Energy losses include tail & diode reverse recovery
$t_{d(on)}$	Turn-On delay time	—	50	70	ns	I_C = 75A, V_{CC} = 400V, V_{GE} = 15V
t_r	Rise time	—	80	100		R_G = 10Ω, L = 100µH
$t_{d(off)}$	Turn-Off delay time	—	200	230		TJ = 25°C
t_f	Fall time	—	60	80		
E_{on}	Turn-On Switching Loss	—	6210	—	µJ	I_C = 75A, V_{CC} = 400V, V_{GE}=15V
E_{off}	Turn-Off Switching Loss	—	2815	—		R_G=10Ω, L=100µH, T_J = 175°C
E_{total}	Total Switching Loss	—	9025	—		Energy losses include tail & diode reverse recovery
$t_{d(on)}$	Turn-On delay time	—	45	—	ns	I_C = 75A, V_{CC} = 400V, V_{GE}=15V
t_r	Rise time	—	70	—		R_G=10Ω, L=100µH
$t_{d(off)}$	Turn-Off delay time	—	240	—		T_J = 175°C
t_f	Fall time	—	80	—		
C_{ies}	Input Capacitance	—	4470	—	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	—	350	—		V_{CC} = 30V
C_{res}	Reverse Transfer Capacitance	—	140	—		f = 1.0Mhz
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T_J = 175°C, I_C = 300A V_{CC} = 480V, Vp ≤600V Rg = 10Ω, V_{GE} = +20V to 0V
SCSOA	Short Circuit Safe Operating Area	5	—	—	µs	V_{CC} = 400V, Vp ≤600V Rg = 10Ω, V_{GE} = +15V to 0V
Erec	Reverse Recovery Energy of the Diode	—	680	—	µJ	T_J = 175°C
t_{rr}	Diode Reverse Recovery Time	—	240	—	ns	V_{CC} = 400V, I_F = 75A
I_{rr}	Peak Reverse Recovery Current	—	50	—	A	V_{GE} = 15V, Rg = 10Ω, L =100µH

Notes:

① V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 100µH, R_G = 50Ω, tested in production I_{LM} ≤ 400A.
② Pulse width limited by max. junction temperature.
③ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.
④ R_θ is measured at T_J of approximately 90°C.
⑤ Calculated continuous current based on maximum allowable junction temperature. Package IGBT current limit is 120A. Package diode current limit is120A. Note that current limitations arising from heating of the device leads may occur.

Qualification Information†

<table>
<tr><td rowspan="2" colspan="2">Qualification Level</td><td colspan="2">Automotive
(per AEC-Q101)</td></tr>
<tr><td colspan="2">Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.</td></tr>
<tr><td rowspan="2" colspan="2">Moisture Sensitivity Level</td><td>TO-247AC</td><td rowspan="2">N/A</td></tr>
<tr><td>TO-247AD</td></tr>
<tr><td rowspan="3">ESD</td><td>Machine Model</td><td colspan="2">Class M4 (+/-425V) ††
AEC-Q101-002</td></tr>
<tr><td>Human Body Model</td><td colspan="2">Class H2 (+/-4000V) ††
AEC-Q101-001</td></tr>
<tr><td>Charged Device Model</td><td colspan="2">Class C5 (+/-1125V) ††
AEC-Q101-005</td></tr>
<tr><td colspan="2">RoHS Compliant</td><td colspan="2">Yes</td></tr>
</table>

† Qualification standards can be found at International Rectifier's web site: http//www.irf.com/

†† Highest passing voltage

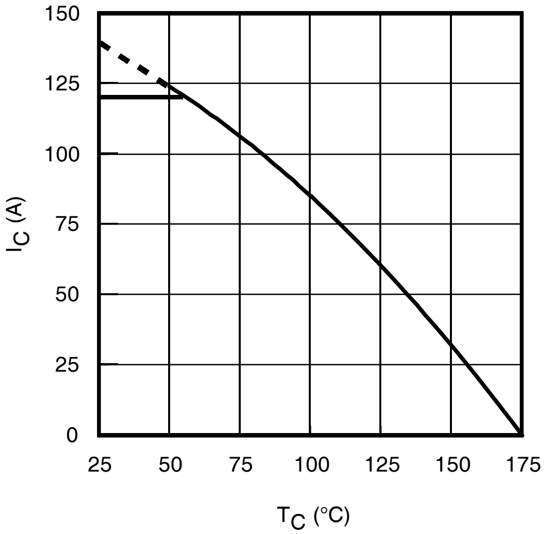


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

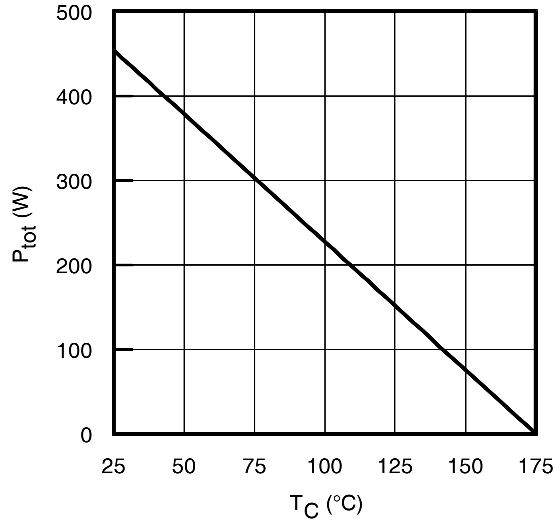


Fig. 2 - Power Dissipation vs. Case Temperature

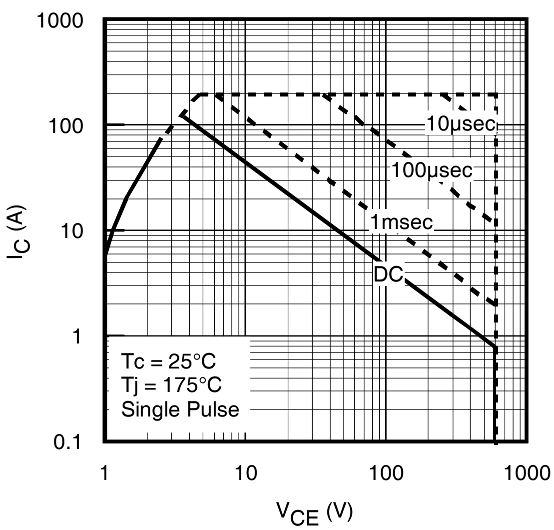


Fig. 3 - Forward SOA
$T_C = 25°C$, $T_J \leq 175°C$; $V_{GE} = 15V$

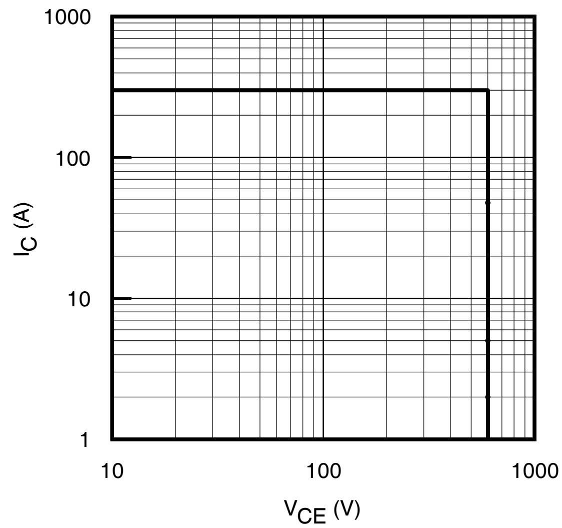


Fig. 4 - Reverse Bias SOA
$T_J = 175°C$; $V_{GE} = 20V$

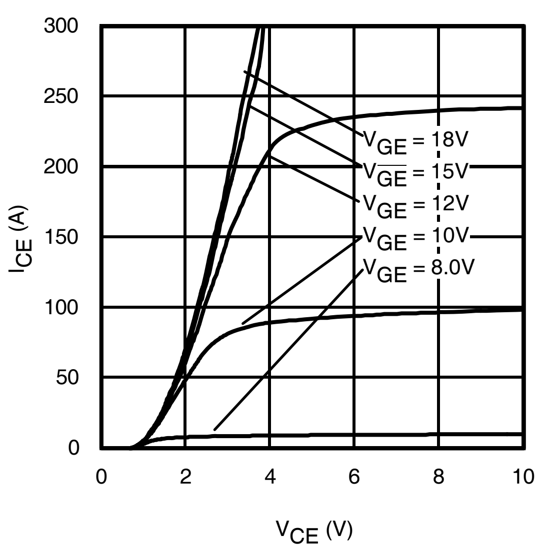


Fig. 5 - Typ. IGBT Output Characteristics
$T_J = -40°C$; tp = ≤60μs

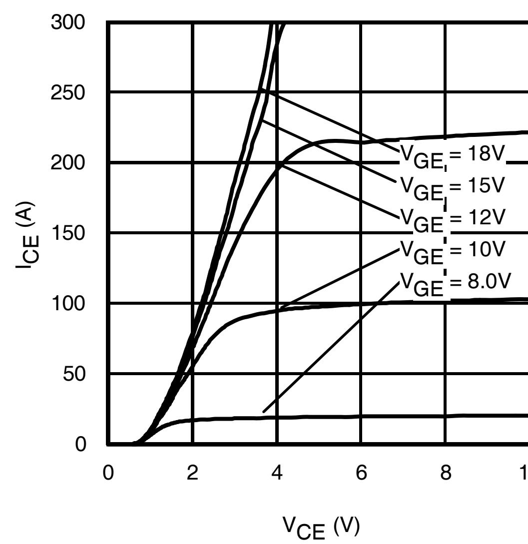


Fig. 6 - Typ. IGBT Output Characteristics
$T_J = 25°C$; tp = ≤60μs

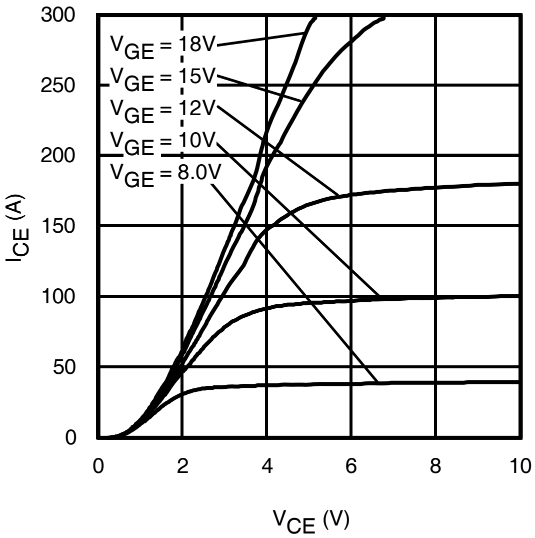


Fig. 7 - Typ. IGBT Output Characteristics
T_J = 175°C; tp = ≤60µs

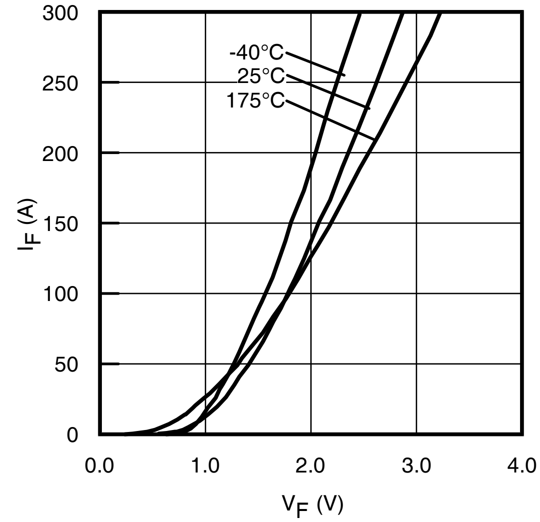


Fig. 8 - Typ. Diode Forward Characteristics
tp = ≤60µs

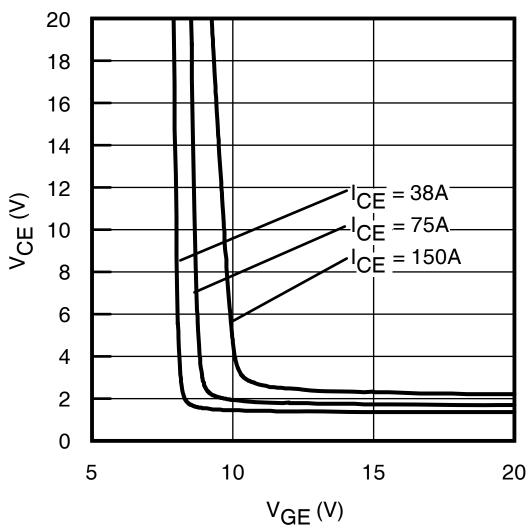


Fig. 9 - Typical V_{CE} vs. V_{GE}
T_J = -40°C

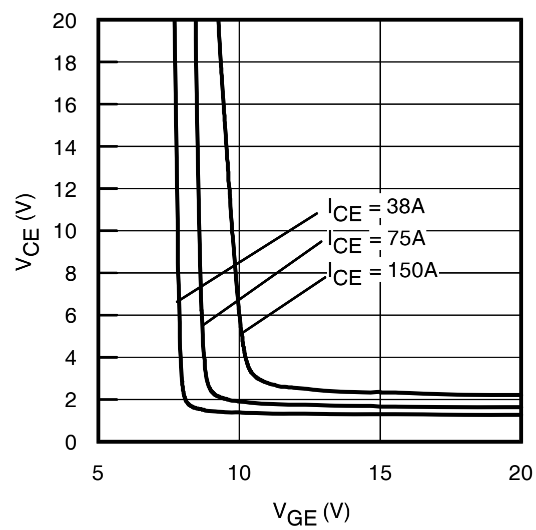


Fig. 10 - Typical V_{CE} vs. V_{GE}
T_J = 25°C

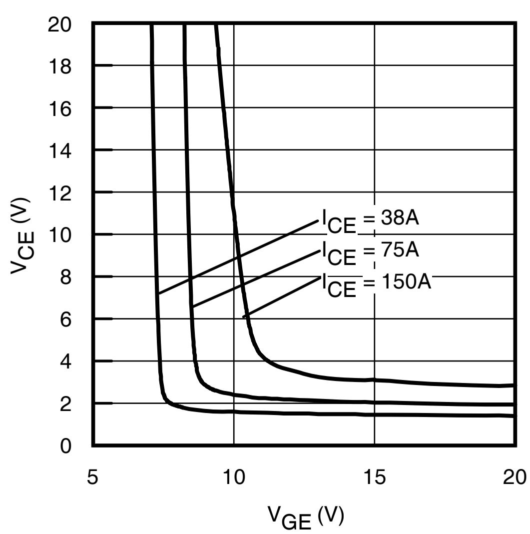


Fig. 11 - Typical V_{CE} vs. V_{GE}
T_J = 175°C

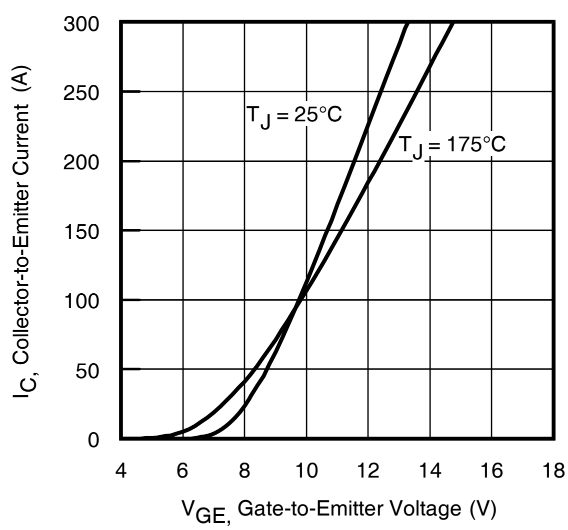


Fig. 12 - Typ. Transfer Characteristics
V_{CE} = 50V; tp = ≤60µs

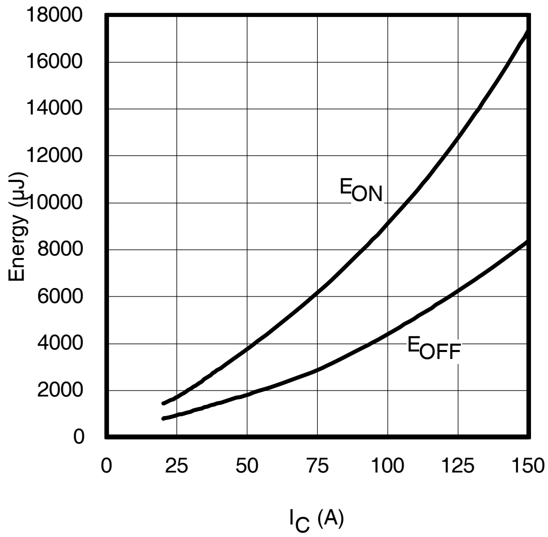


Fig. 13 - Typ. Energy Loss vs. I_C
$T_J = 175°C$; L = 100µH; $V_{CE} = 400V$, $R_G = 10\Omega$; $V_{GE} = 15V$

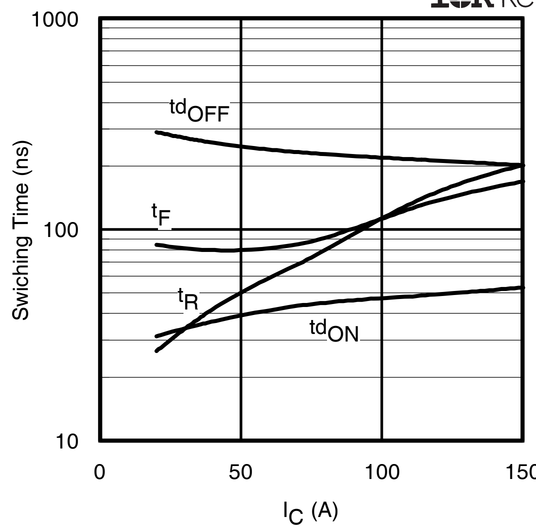


Fig. 14 - Typ. Switching Time vs. I_C
$T_J = 175°C$; L = 100µH; $V_{CE} = 400V$, $R_G = 10\Omega$; $V_{GE} = 15V$

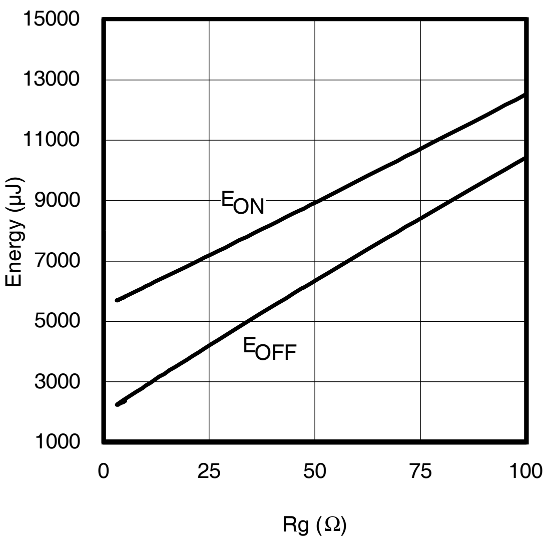


Fig. 15 - Typ. Energy Loss vs. R_G
$T_J = 175°C$; L = 100µH; $V_{CE} = 400V$, $I_{CE} = 75A$; $V_{GE} = 15V$

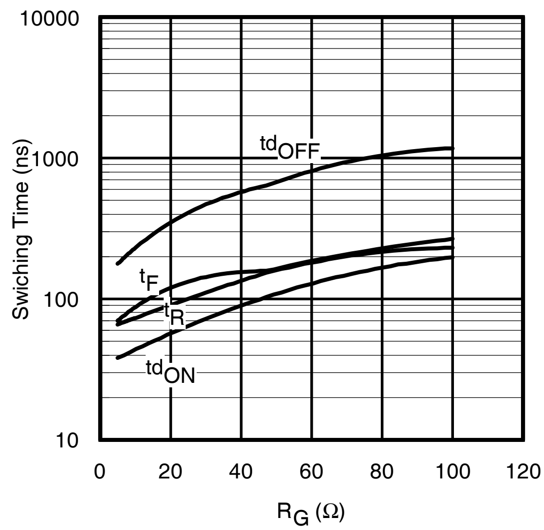


Fig. 16 - Typ. Switching Time vs. R_G
$T_J = 175°C$; L = 100µH; $V_{CE} = 400V$, $I_{CE} = 75A$; $V_{GE} = 15V$

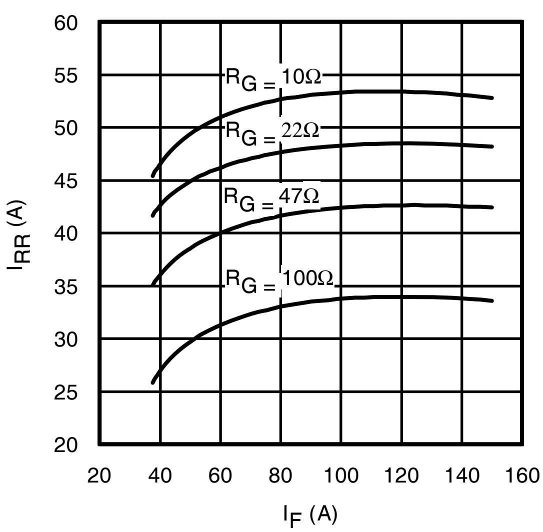


Fig. 17 - Typ. Diode I_{RR} vs. I_F
$T_J = 175°C$

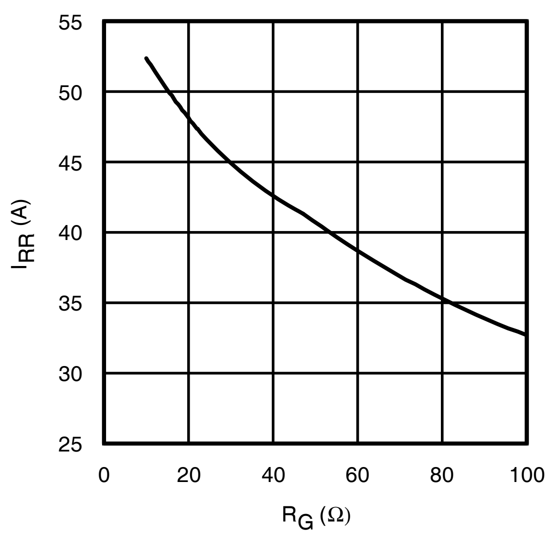


Fig. 18 - Typ. Diode I_{RR} vs. R_G
$T_J = 175°C$

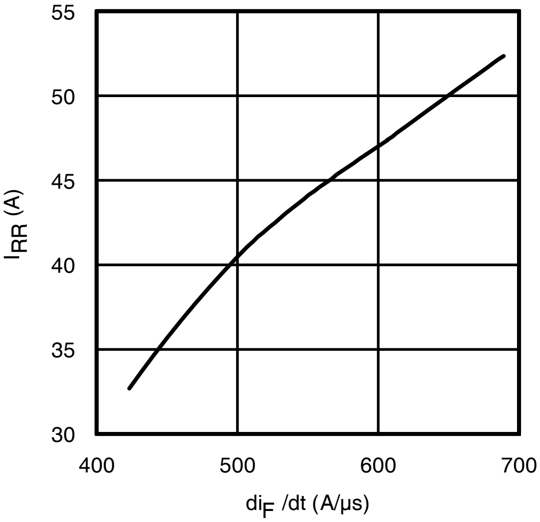


Fig. 19 - Typ. Diode I_{RR} vs. di_F/dt
V_{CC} = 400V; V_{GE} = 15V; I_F = 75A; T_J = 175°C

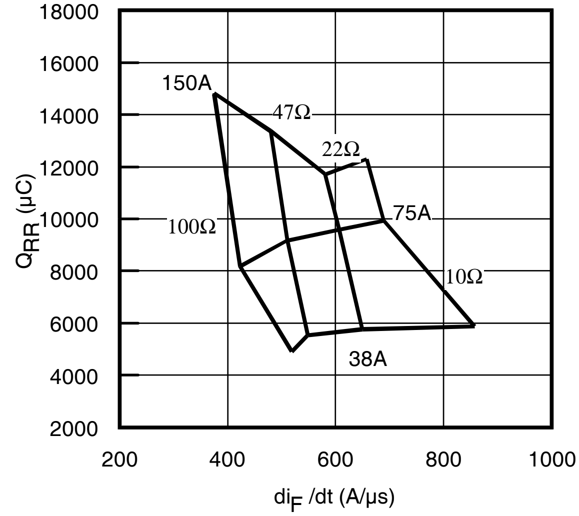


Fig. 20 - Typ. Diode Q_{RR} vs. di_F/dt
V_{CC} = 400V; V_{GE} = 15V; T_J = 175°C

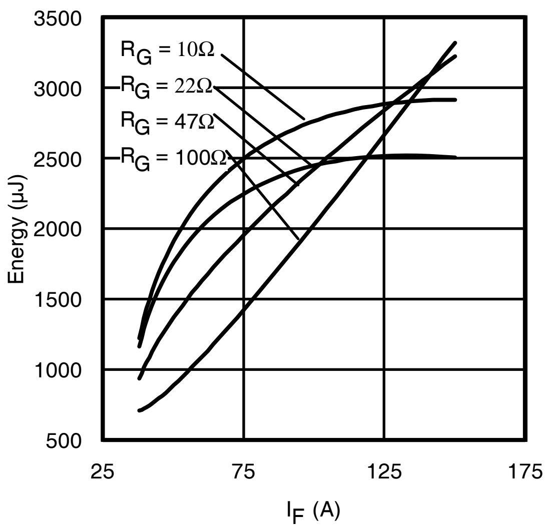


Fig. 21 - Typ. Diode E_{RR} vs. I_F
T_J = 175°C

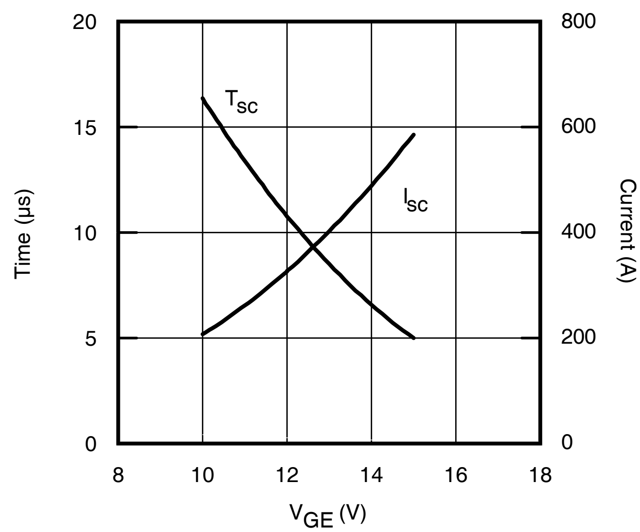


Fig. 22 - V_{GE} vs. Short Circuit Time
V_{CC} = 400V; T_C = 25°C

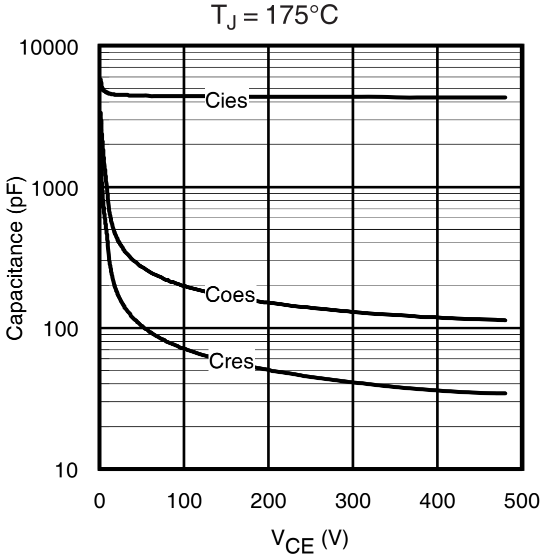


Fig. 23 - Typ. Capacitance vs. V_{CE}
V_{GE}= 0V; f = 1MHz

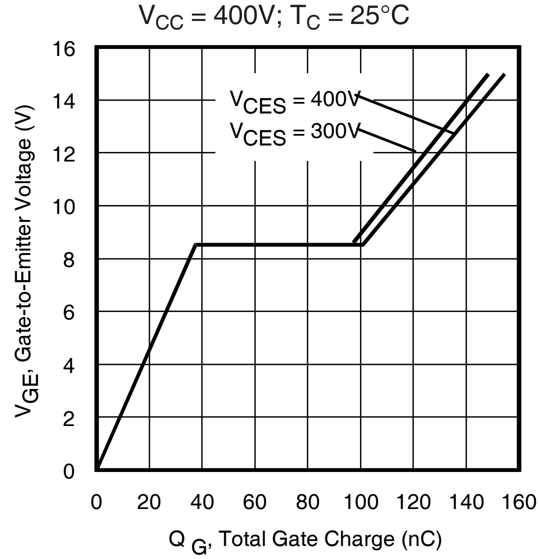
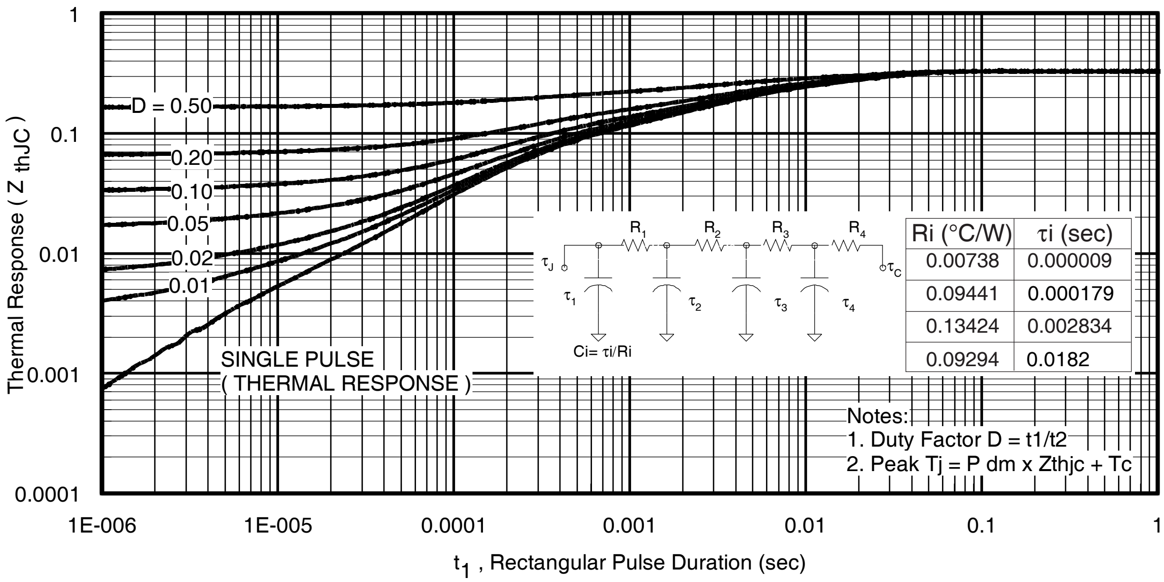
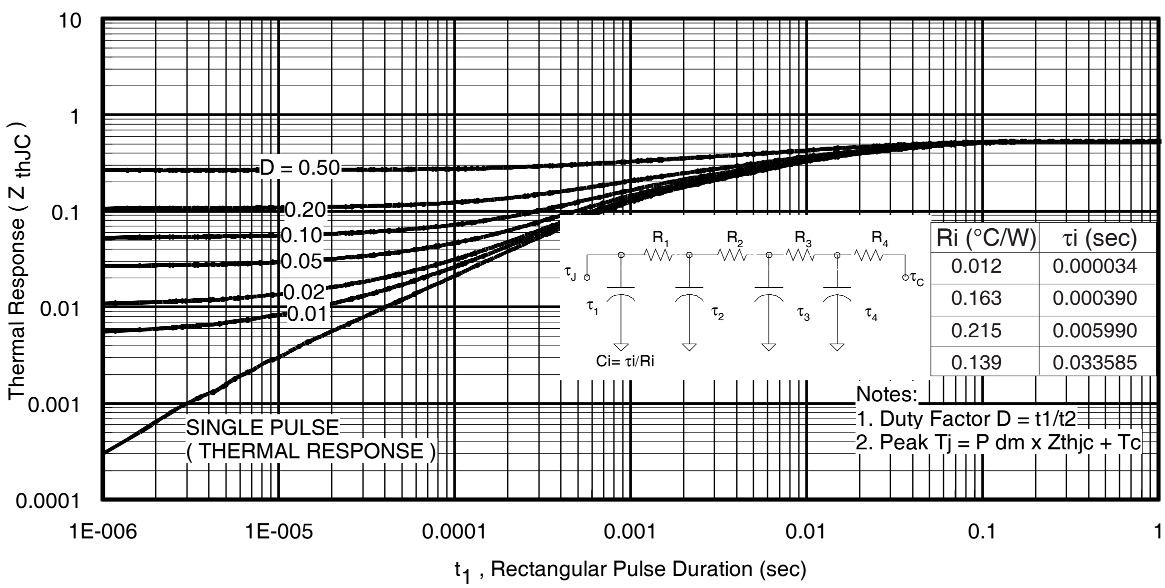


Fig. 24 - Typical Gate Charge vs. V_{GE}
I_{CE} = 75A; L = 485µH



Ri (°C/W)	τi (sec)
0.00738	0.000009
0.09441	0.000179
0.13424	0.002834
0.09294	0.0182

Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)



Ri (°C/W)	τi (sec)
0.012	0.000034
0.163	0.000390
0.215	0.005990
0.139	0.033585

Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

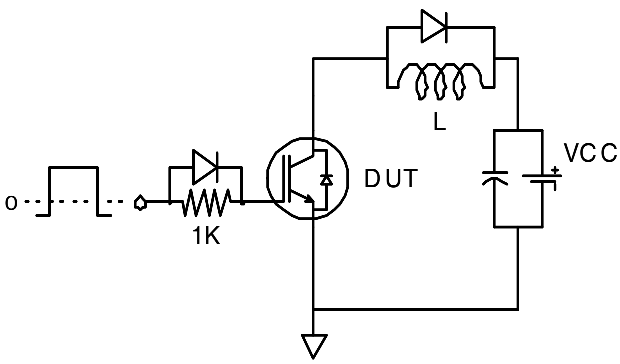


Fig.C.T.1 - Gate Charge Circuit (turn-off)

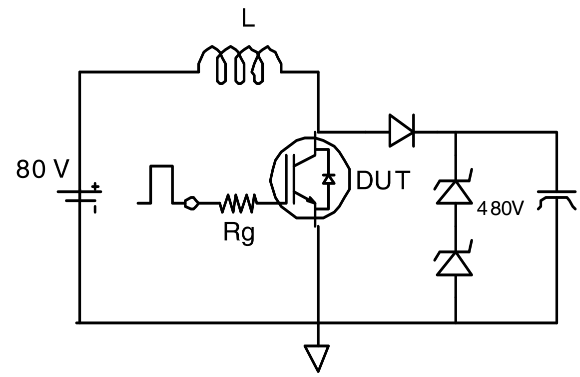


Fig.C.T.2 - RBSOA Circuit

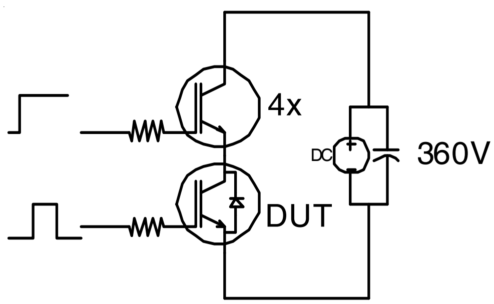


Fig.C.T.3 - S.C. SOA Circuit

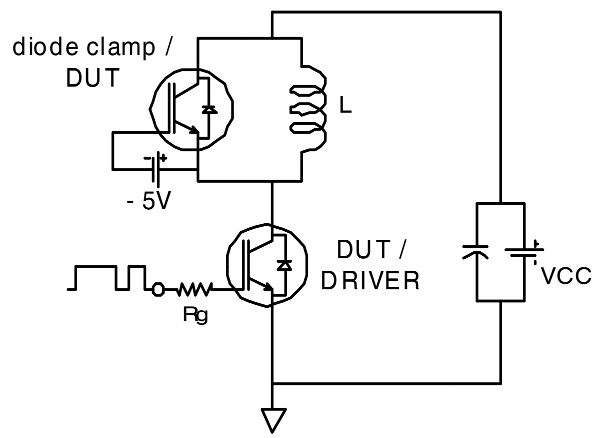


Fig.C.T.4 - Switching Loss Circuit

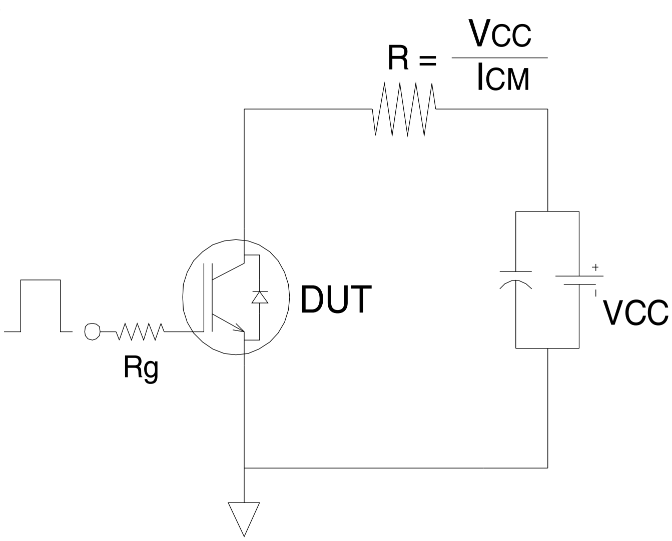


Fig.C.T.5 - Resistive Load Circuit

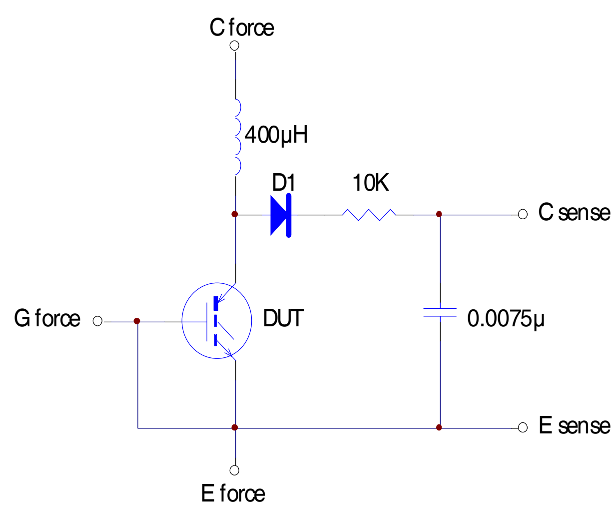


Fig.C.T.6 - BVCES Filter Circuit

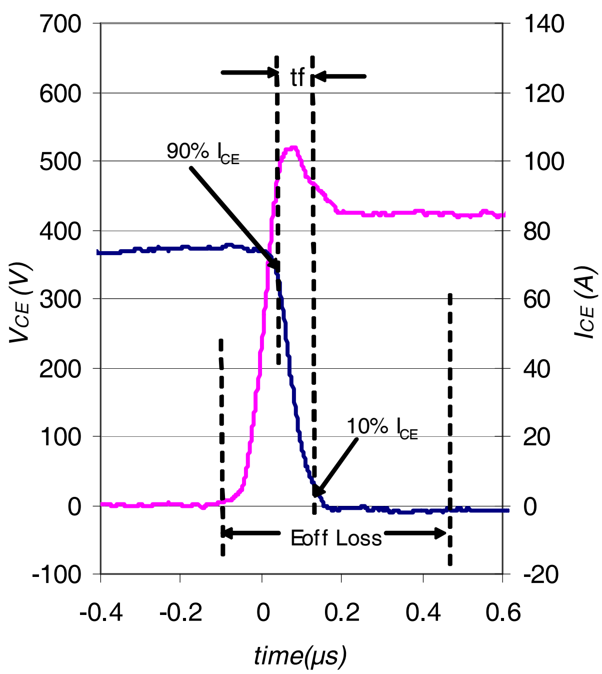


Fig. WF1 - Typ. Turn-off Loss Waveform
@ T_J = 175°C using Fig. CT.4

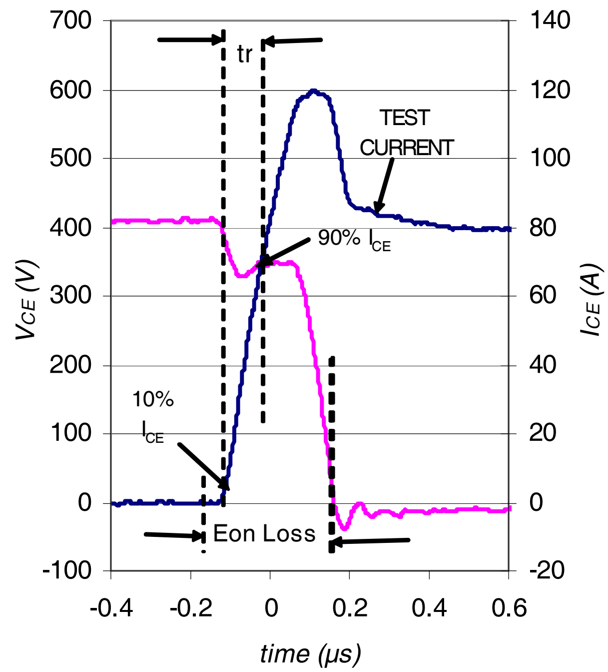


Fig. WF2 - Typ. Turn-on Loss Waveform
@ T_J = 175°C using Fig. CT.4

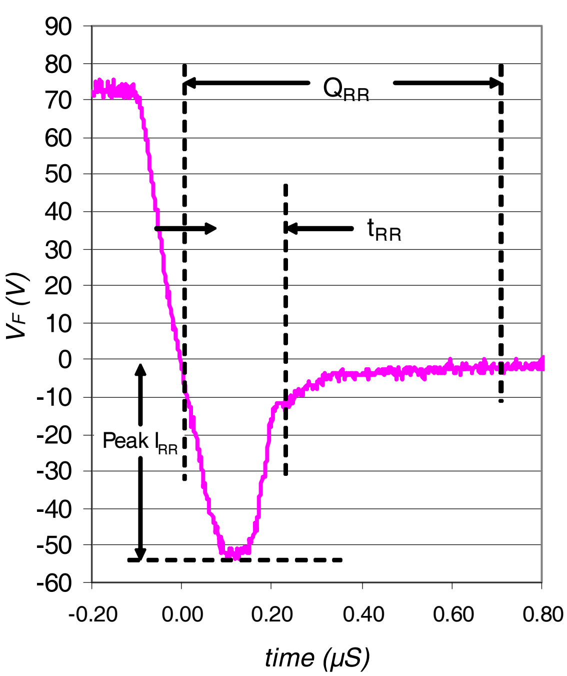


Fig. WF3 - Typ. Diode Recovery Waveform
@ T_J = 175°C using Fig. CT.4

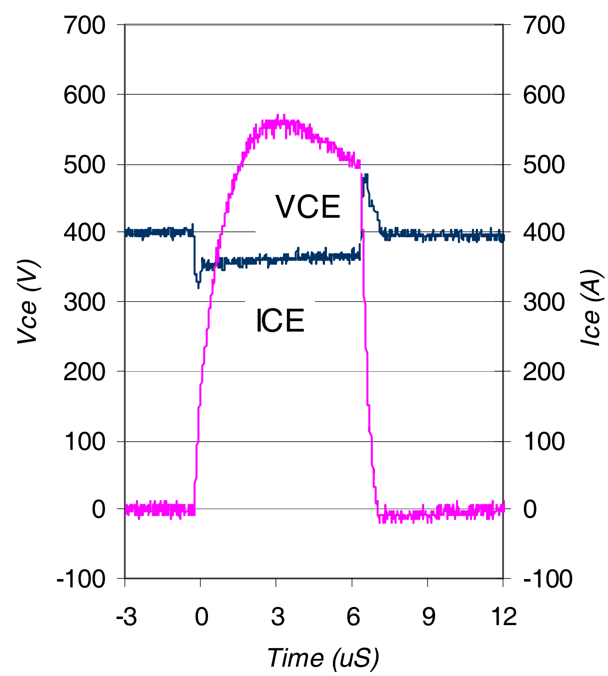
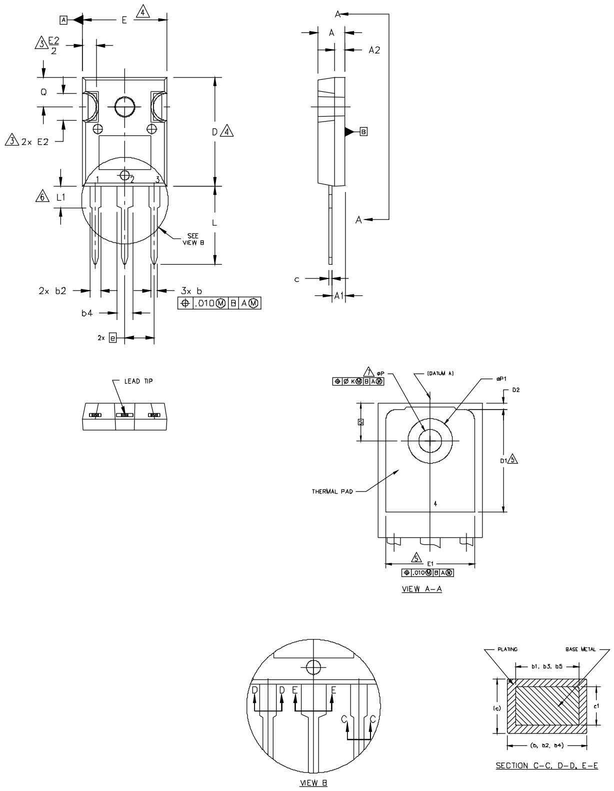


Fig. WF4 - Typ. S.C. Waveform
@ T_J = 25°C using Fig. CT.3

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. øP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	–	13.08	–	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	–	13.46	–	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
øP	.140	.144	3.56	3.66	
øP1	–	.291	–	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

1.– GATE
2.– DRAIN
3.– SOURCE
4.– DRAIN

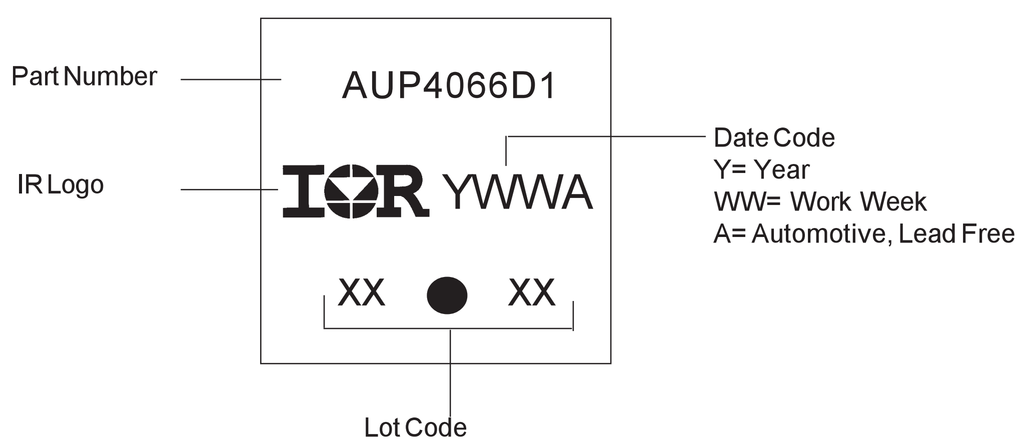
IGBTs, CoPACK

1.– GATE
2.– COLLECTOR
3.– EMITTER
4.– COLLECTOR

DIODES

1.– ANODE/OPEN
2.– CATHODE
3.– ANODE

TO-247AC Part Marking Information

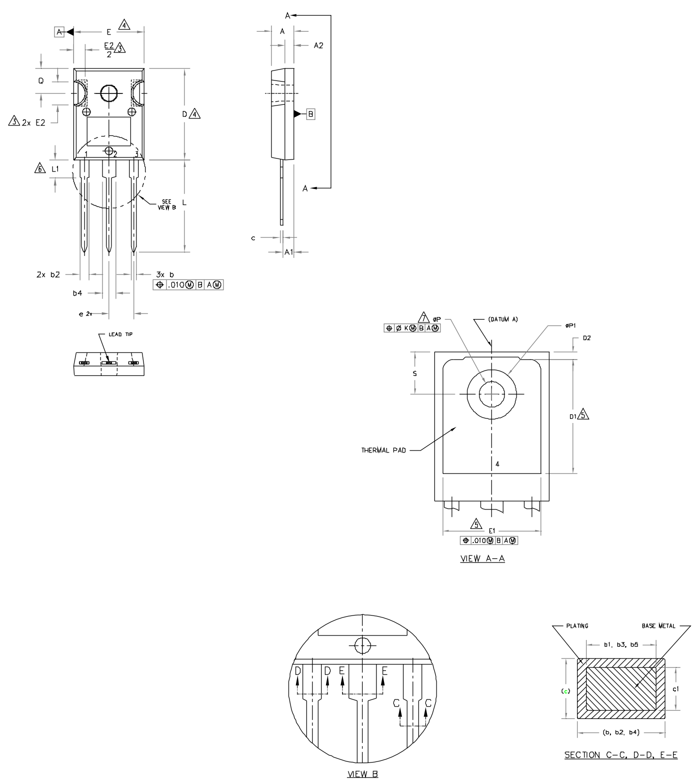


TO-247AC package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

TO-247AD Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.190	.203	4.83	5.13	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	–	13.08	–	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	–	13.46	–	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	–	.291	–	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

1.- GATE
2.- DRAIN
3.- SOURCE
4.- DRAIN

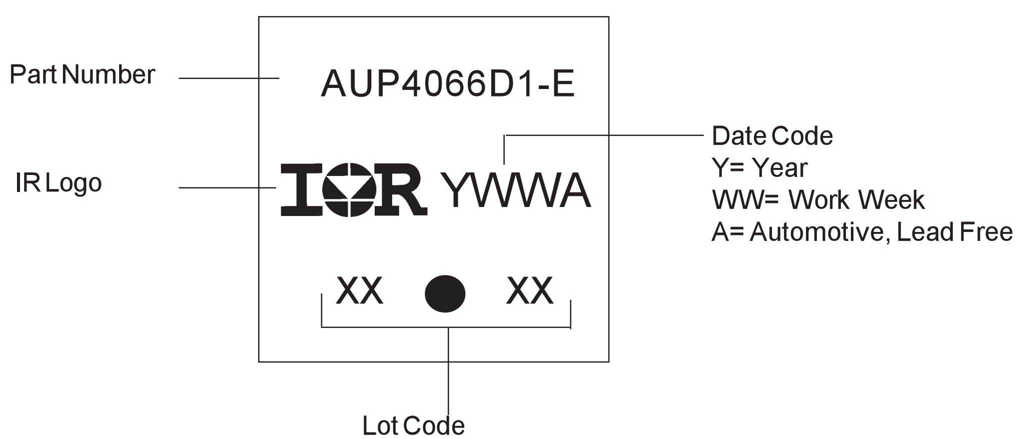
IGBTs, CoPACK

1.- GATE
2.- COLLECTOR
3.- EMITTER
4.- COLLECTOR

DIODES

1.- ANODE/OPEN
2.- CATHODE
3.- ANODE

TO-247AD Part Marking Information



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRGP4066D1	TO-247AC	Tube	25	AUIRGP4066D1
AUIRGP4066D1-E	TO-247AD	Tube	25	AUIRGP4066D1-E

IMPORTANT NOTICE

Unless specifically designated for the automotive market, International Rectifier Corporation and its subsidiaries (IR) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or services without notice. Part numbers designated with the “AU” prefix follow automotive industry and / or customer specific requirements with regards to product discontinuance and process change notification. All products are sold subject to IR’s terms and conditions of sale supplied at the time of order acknowledgment.

IR warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with IR’s standard warranty. Testing and other quality control techniques are used to the extent IR deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

IR assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using IR components. To minimize the risks with customer products and applications, customers should provide adequate design and operating safeguards.

Reproduction of IR information in IR data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alterations is an unfair and deceptive business practice. IR is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of IR products or serviced with statements different from or beyond the parameters stated by IR for that product or service voids all express and any implied warranties for the associated IR product or service and is an unfair and deceptive business practice. IR is not responsible or liable for any such statements.

IR products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or in other applications intended to support or sustain life, or in any other application in which the failure of the IR product could create a situation where personal injury or death may occur. Should Buyer purchase or use IR products for any such unintended or unauthorized application, Buyer shall indemnify and hold International Rectifier and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that IR was negligent regarding the design or manufacture of the product.

Only products certified as military grade by the Defense Logistics Agency (DLA) of the US Department of Defense, are designed and manufactured to meet DLA military specifications required by certain military, aerospace or other applications. Buyers acknowledge and agree that any use of IR products not certified by DLA as military-grade, in applications requiring military grade products, is solely at the Buyer’s own risk and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

IR products are neither designed nor intended for use in automotive applications or environments unless the specific IR products are designated by IR as compliant with ISO/TS 16949 requirements and bear a part number including the designation “AU”. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, IR will not be responsible for any failure to meet such requirements.

For technical support, please contact IR’s Technical Assistance Center

http://www.irf.com/technical-info/

WORLD HEADQUARTERS:

101 N. Sepulveda Blvd., El Segundo, California 90245

Tel: (310) 252-7105

Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург, Промышленная ул, дом № 19, литера Н, помещение 100-Н Офис 331